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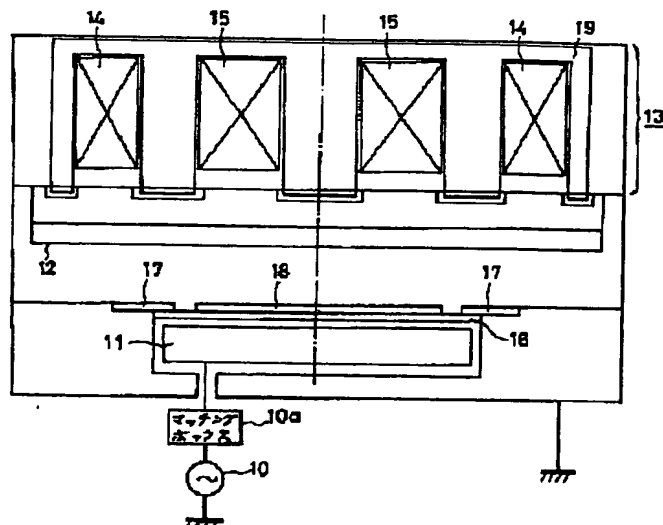
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TITLE : PLASMA DAMAGE REDUCTION AND
PLASMA PROCESSOR



ABSTRACT : PURPOSE: To reduce the generation of plasma damage such as gate leakage in etching using a high frequency plasma processor of magnetic field impressing type.

CONSTITUTION: A plasma processor, where a high frequency electric field is impressed onto a substrate electrode 11 to generate plasma, and further a magnetic field is impressed onto this plasma by an electromagnet unit 13 to etch a sample wafer 18 mounted on the substrate electrode 11, is so constituted that the inclination of an intensity distribution of an impressed magnetic field on the sample wafer 18 on the substrate electrode 11 may be zeroized. This design can reduce plasma damage in etching while securing etching speed and its uniformity.

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